



SLP11N35UZ / SLF11N35UZ

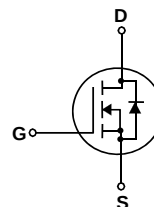
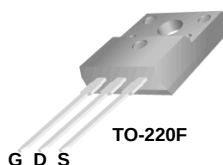
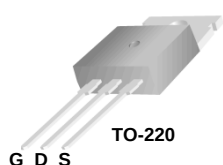
350V N-Channel MOSFET

General Description

This Power MOSFET is produced using Maple semi's advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

- 11A, 350V, $R_{DS(on)typ.} = 0.460\Omega @ V_{GS} = 10V$
- Low gate charge (typical 29nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	SLP11N35UZ	SLF11N35UZ	Units
V_{DSS}	Drain-Source Voltage	350		V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	11	11 *	A
	- Continuous ($T_C = 100^\circ\text{C}$)	6.6	6.6 *	A
I_{DM}	Drain Current - Pulsed (Note 1)	44	44 *	A
V_{GSS}	Gate-Source Voltage	± 25		V
EAS	Single Pulsed Avalanche Energy (Note 2)	360		mJ
I_{AR}	Avalanche Current (Note 1)	11		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	16.70		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	167	38.5	W
	- Derate above 25°C	1.3	0.31	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	SLP11N35UZ	SLF11N35UZ	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.75	3.25	$^\circ\text{C/W}$
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C/W}$

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	350	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.35	--	$V/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 350\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 280\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	--	--	10	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$	--	--	-10	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}$	--	460	550	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 5.5\text{ A}$ (Note 4)	--	8	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1132	--	pF
C_{oss}	Output Capacitance		--	164	--	pF
C_{rss}	Reverse Transfer Capacitance		--	4	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 175\text{ V}, I_D = 11\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4, 5)	--	30.5	--	ns
t_r	Turn-On Rise Time		--	34.5	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	113.5	--	ns
t_f	Turn-Off Fall Time		--	37.5	--	ns
Q_g	Total Gate Charge	$V_{DS} = 280\text{ V}, I_D = 11\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	29	--	nC
Q_{gs}	Gate-Source Charge		--	6.7	--	nC
Q_{gd}	Gate-Drain Charge		--	12.5	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	11	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	44	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 11 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 11 A,	--	400	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/us (Note 4)	--	3.8	--	uC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 5.7\text{ mH}, I_{AS} = 11\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 11\text{ A}, di/dt \leq 100\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

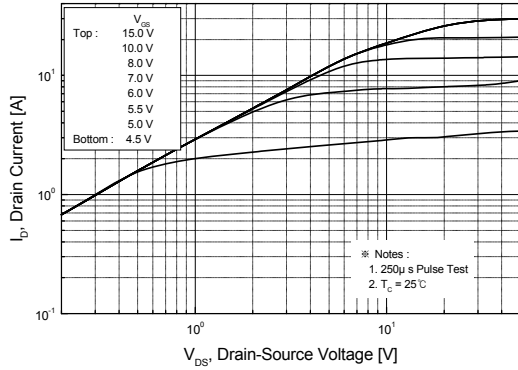


Figure 1. On-Region Characteristics

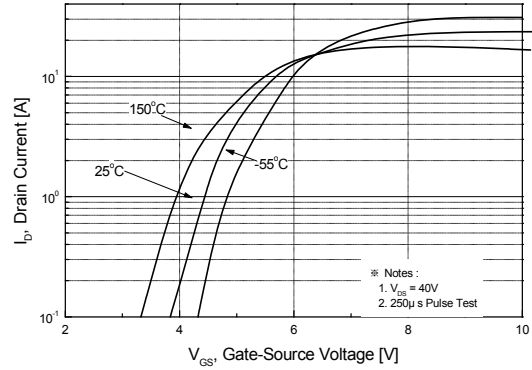


Figure 2. Transfer Characteristics

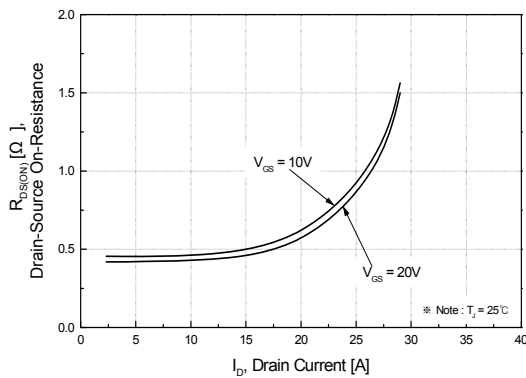


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

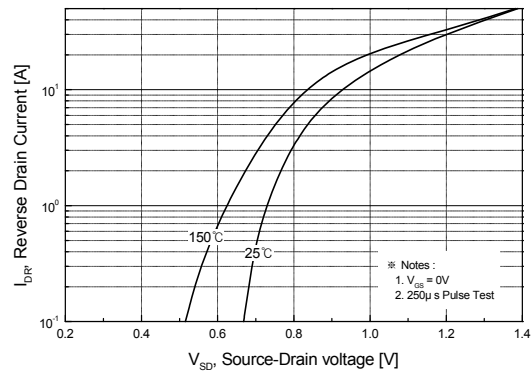


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

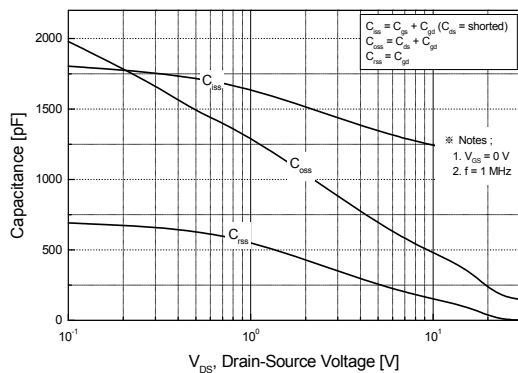


Figure 5. Capacitance Characteristics

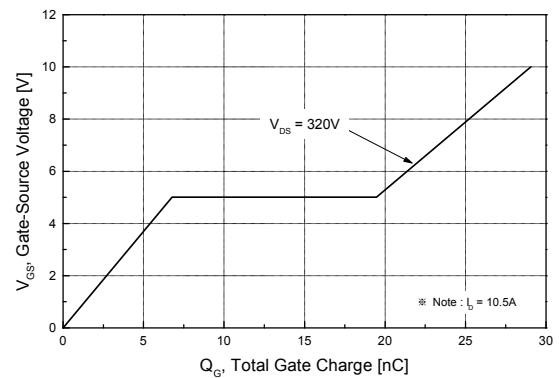


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

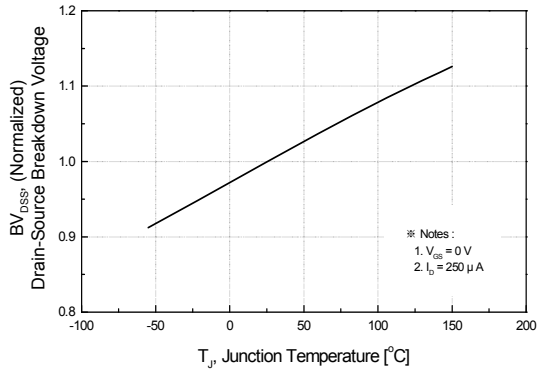


Figure 7. Breakdown Voltage Variation vs Temperature

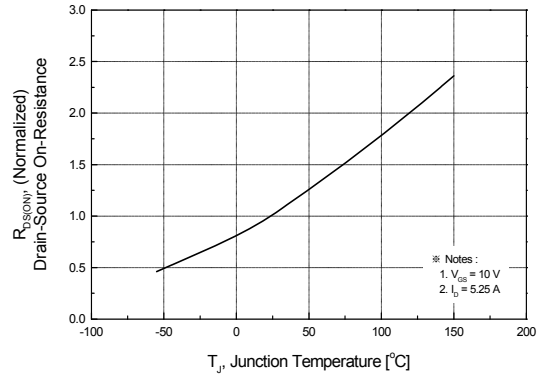


Figure 8. On-Resistance Variation vs Temperature

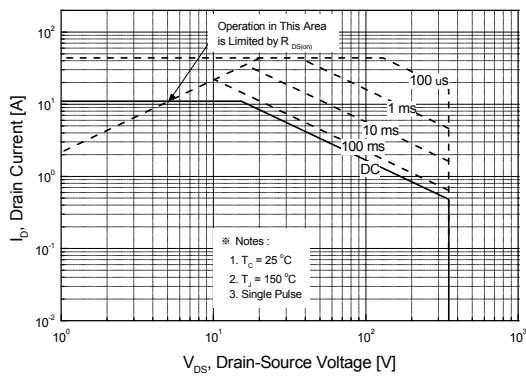


Figure 9-1. Maximum Safe Operating Area for SLP11N35UZ

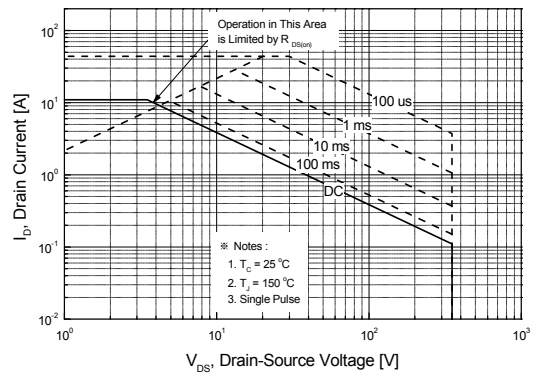


Figure 9-2. Maximum Safe Operating Area for SLF11N35UZ

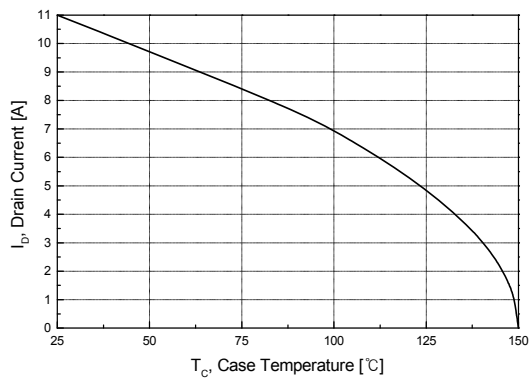


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

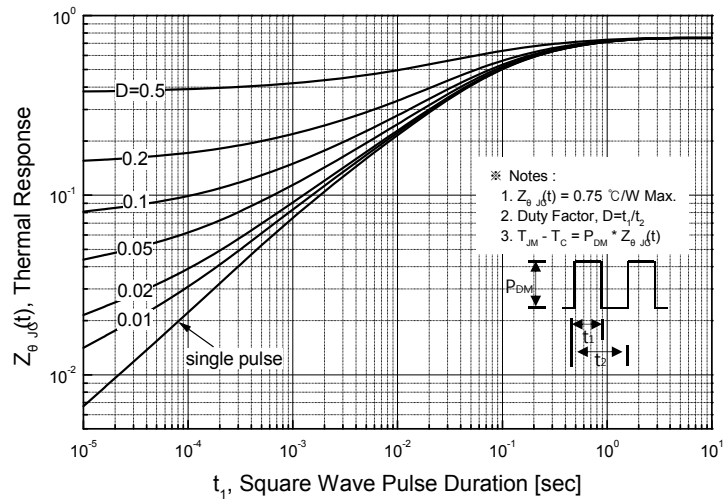


Figure 11-1. Transient Thermal Response Curve for SLP11N35UZ

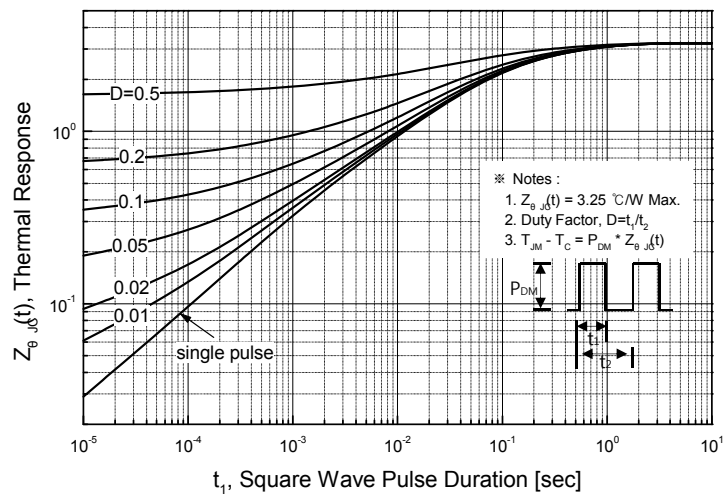
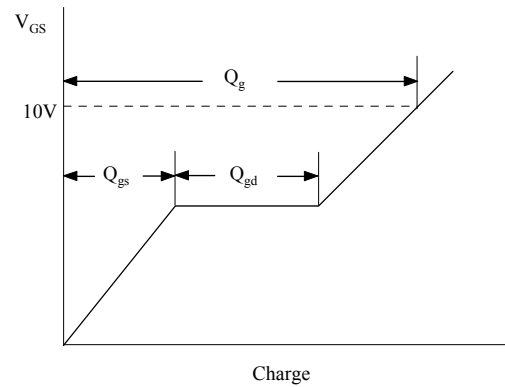
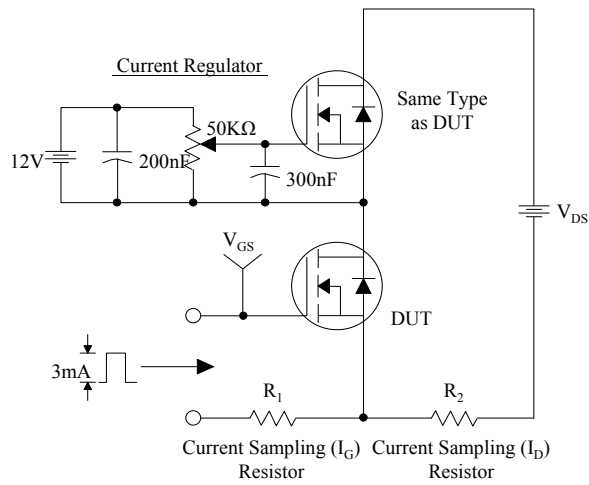
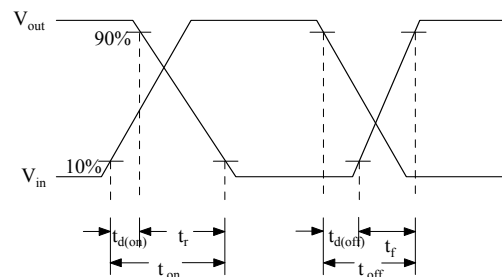
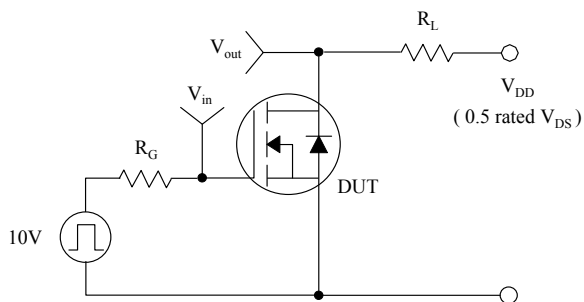


Figure 11-2. Transient Thermal Response Curve for SLF11N35UZ

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

